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- Low $r_{DS(on)} \dots 1.3 \Omega$ Typical
- Avalanche Energy . . . 75 mJ
- Eight Power DMOS Transistor Outputs of 250-mA Continuous Current
- 1.5-A Pulsed Current Per Output
- Output Clamp Voltage at 45 V
- Devices Are Cascadable
- Low Power Consumption

description

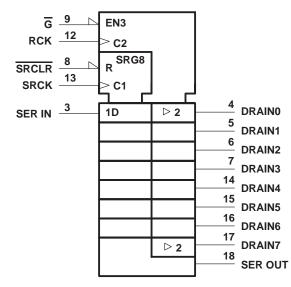
The TPIC6595 is a monolithic, high-voltage, highcurrent power 8-bit shift register designed for use in systems that require relatively high load power. The device contains a built-in voltage clamp on the outputs for inductive transient protection. Power driver applications include relays, solenoids, and other medium-current or high-voltage loads.

This device contains an 8-bit serial-in, parallel-out shift register that feeds an 8-bit D-type storage register. Data transfers through both the shift and storage registers on the rising edge of the shift-register clock (SRCK) and the register clock (RCK) respectively. The storage register transfers data to the output buffer when shift-register clear (SRCLR) is high. When SRCLR is low, the input shift register is cleared. When output enable (\overline{G}) is held high, all data in the output buffers is held low and all drain outputs are off. When \overline{G} is held low, data from the storage register is transparent to the output buffers. The serial output (SER OUT) allows for cascading of the data from the shift register to additional devices.

Outputs are low-side, open-drain DMOS transistors with output ratings of 45 V and 250-mA

| DW OR N PACKAGE (TOP VIEW) | | | | | | | | | | |
|-------------------------------|-----|----------|---------|--|--|--|--|--|--|--|
| | | <u> </u> | | | | | | | | |
| PGND [| 1 U | 20 | PGND | | | | | | | |
| Vcc[| 2 | 19 | LGND | | | | | | | |
| SER IN | 3 | 18 | SER OUT | | | | | | | |
| DRAIN0 | 4 | 17 | DRAIN7 | | | | | | | |
| DRAIN1 | 5 | 16 | DRAIN6 | | | | | | | |
| DRAIN2 | 6 | 15 | DRAIN5 | | | | | | | |
| DRAIN3 | 7 | 14 | DRAIN4 | | | | | | | |
| SRCLR | 8 | 13 | SRCK | | | | | | | |
| G | 9 | 12 | RCK | | | | | | | |
| PGND | 10 | 11 | PGND | | | | | | | |

logic symbol[†]



[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

continuous sink current capability. When data in the output buffers is low, the DMOS-transistor outputs are off. When data is high, the DMOS-transistor outputs have sink current capability.

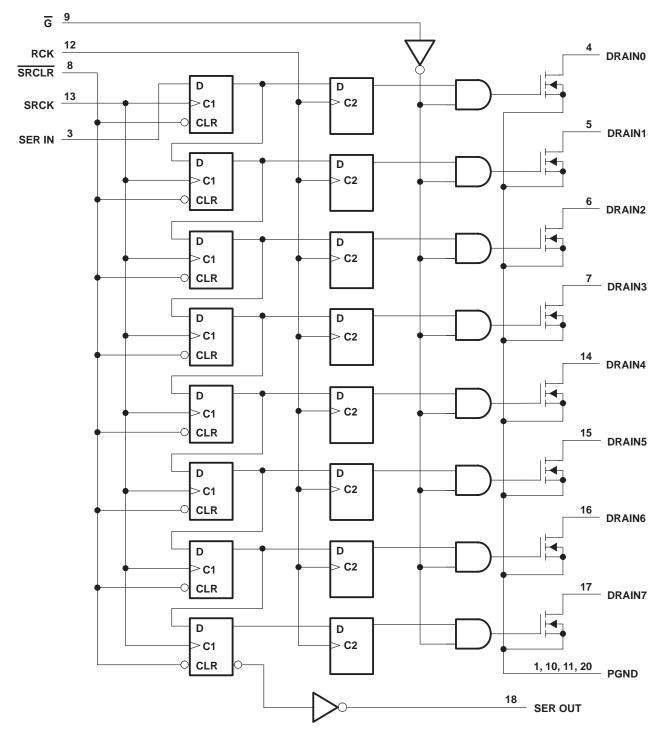
Separate power and logic level ground pins are provided to facilitate maximum system flexibility. Pins 1, 10, 11, and 20 are internally connected, and each pin must be externally connected to the power system ground in order to minimize parasitic inductance. A single-point connection between pin 19, logic ground (LGND), and pins 1, 10, 11, and 20, power grounds (PGND), must be externally made in a manner that reduces crosstalk between the logic and load circuits.

The TPIC6595 is characterized for operation over the operating case temperature range of -40°C to 125°C.



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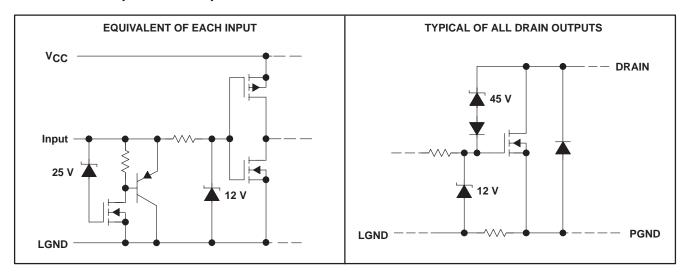
logic diagram (positive logic)





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schematic of inputs and outputs



absolute maximum ratings over recommended operating case temperature range (unless otherwise noted)^{\dagger}

| Logic supply voltage, V _{CC} (see Note 1) | |
|--|----------------|
| Logic input voltage range, V _I | –0.3 V to 7 V |
| Power DMOS drain-to-source voltage, V _{DS} (see Note 2) | |
| Continuous source-drain diode anode current | 1 A |
| Pulsed source-drain diode anode current | |
| Pulsed drain current, each output, all outputs on, I_{Dn} , $T_A = 25^{\circ}C$ (see Note 3) | 750 mA |
| Continuous drain current, each output, all outputs on, IDn, TA = 25°C | 250 mA |
| Peak drain current single output, I _{DM} , T _A = 25°C (see Note 3) | |
| Single-pulse avalanche energy, EAS (see Note 4) | |
| Avalanche current, I _{AS} (see Note 4) | 1 A |
| Continuous total power dissipation | |
| Operating virtual junction temperature range, T ₁ | –40°C to 150°C |
| Storage temperature range, T _{stg} | |
| Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds | |

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values are with respect to LGND and PGND.
 - 2. Each power DMOS source is internally connected to PGND.
 - 3. Pulse duration \leq 100 µs, duty cycle \leq 2 %

4. DRAIN supply voltage = 15 V, starting junction temperature (T_{JS}) = 25° C, L = 100 mH, I_{AS} = 1 A (see Figure 4).

DISSIPATION RATING TABLE

| PACKAGE | T _A ≤ 25°C POWER RATING | DERATING FACTOR ABOVE T _A = 25°C | T _A = 125°C POWER RATING |
|---------|---------------------------------------|--|--|
| DW | 1125 mW | 9.0 mW/°C | 225 mW |
| Ν | 1150 mW | 9.2 mW/°C | 230 mW |



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recommended operating conditions over recommended operating temperature range (unless otherwise noted)

| | MIN | MAX | UNIT |
|---|----------------------|----------------------|------|
| Logic supply voltage, V _{CC} | 4.5 | 5.5 | V |
| High-level input voltage, VIH | 0.85 V _{CC} | | V |
| Low-level input voltage, VIL | | 0.15 V _{CC} | V |
| Pulsed drain output current, $T_C = 25^{\circ}C$, $V_{CC} = 5 V$ (see Notes 3 and 5) | -1.8 | 1.5 | А |
| Setup time, SER IN high before SRCK [↑] , t _{SU} (see Figure 2) | 10 | | ns |
| Hold time, SER IN high after SRCK [↑] , t _h (see Figure 2) | 10 | | ns |
| Pulse duration, t _W (see Figure 2) | 20 | | ns |
| Operating case temperature, T _C | -40 | 125 | °C |

electrical characteristics, V_{CC} = 5 V, T_{C} = 25°C (unless otherwise noted)

| | PARAMETER | | TEST CONDI | TIONS | MIN | TYP | MAX | UNIT |
|---------------------|---|---|-----------------------------|---|-----|-------|-----|------|
| V(BR)DSX | Drain-source breakdown voltage | I _D = 1 mA | | | 45 | | | V |
| V _{SD} | Source-drain diode forward voltage | I _F = 250 mA, | See Note 3 | | | 0.85 | 1 | V |
| | High-level output voltage, | $I_{OH} = -20 \text{ mA}$ | $V_{\rm CC} = 4.5 \rm V$ | | 4.4 | 4.49 | | V |
| VOH | SER OUT | $I_{OH} = -4 \text{ mA},$ | $V_{CC} = 4.5 V$ | | 4.1 | 4.3 | | V |
| N | Low-level output voltage, SER | I _{OH} = 20 mA, | $V_{CC} = 4.5 V$ | | | 0.002 | 0.1 | V |
| VOL | OUT | $I_{OH} = 4 \text{ mA},$ | $V_{CC} = 4.5 V$ | | | 0.2 | 0.4 | V |
| V _(hys) | Input hysteresis | V _{DS} = 15 V | | | | 1.3 | | V |
| IIН | High-level input current | V _{CC} = 5.5 V, | $V_I = V_{CC}$ | | | | 1 | μA |
| IIГ | Low-level input current | V _{CC} = 5.5 V, | $V_{I} = 0$ | | | | -1 | μA |
| ICCL | Logic supply current | I _O = 0, | All inputs low | | | 15 | 100 | μΑ |
| ICC(FRQ) | Logic supply current frequency | fSRCK = 5 MH See Figures 1, | lz, IO = 0, , 2, and 6 | C _L = 30 pF, | | 0.6 | 5 | mA |
| IN | Nominal current | $V_{DS(on)} = 0.5$ $I_N = I_D$, | V, T _C = 85°C | See Notes 5, 6, and 7 | | 250 | | mA |
| | | V _{DS} = 40 V | | | | 0.05 | 1 | |
| IDSX | Off-state drain current | V _{DS} = 40 V, | T _C = 125°C | | | 0.15 | 5 | μA |
| | | I _D = 250 mA, | $V_{CC} = 4.5 V$ | | | 1.3 | 2 | |
| ^r DS(on) | Static drain-source on-state resistance | I _D = 250 mA, V _{CC} = 4.5 V | T _C = 125°C, | See Notes 5 and 6 and Figures 9 and 10 | | 2 | 3.2 | Ω |
| | | I _D = 500 mA, | V _{CC} = 4.5 V | | | 1.3 | 2 | |

switching characteristics, V_{CC} = 5 V, T_C = 25°C

| | PARAMETER | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|------------------|--|--|-----|-----|-----|------|
| ^t PLH | Propagation delay time, low-to-high-level output from \overline{G} | | | 650 | | ns |
| ^t PHL | Propagation delay time, high-to-low-level output from \overline{G} | C _L = 30 pF, I _D = 250 mA, | | 150 | | ns |
| tr | Rise time, drain output | See Figures 1 and 2 | | 750 | | ns |
| t _f | Fall time, drain output | | | 425 | | ns |
| ta | Reverse-recovery-current rise time | I _F = 250 mA, di/dt = 20 A/μs, | | 100 | | |
| t _{rr} | Reverse-recovery time | See Notes 5 and 6 and Figure 3 | | 300 | | ns |

NOTES: 3. Pulse duration $\leq 100 \,\mu$ s, duty cycle $\leq 2\%$

5. Technique should limit $T_J - T_C$ to 10°C maximum.

6. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.

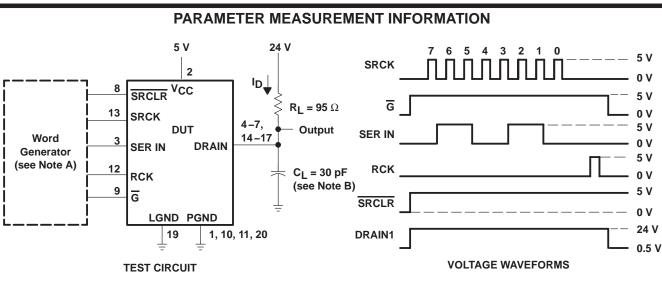
Nominal current is defined for a consistent comparison between devices from different sources. It is the current that produces a voltage drop of 0.5 V at T_C = 85°C.



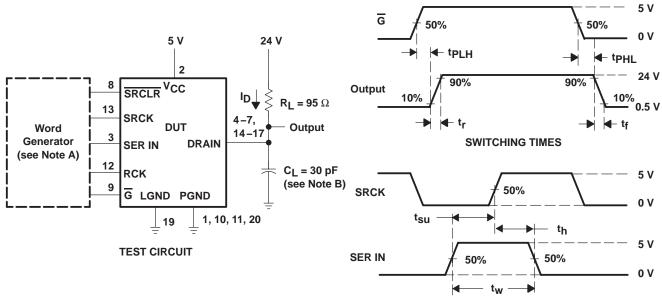
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thermal resistance

| | PARAMETER | TEST CONDITIONS | MIN | MAX | UNIT | |
|--|--|--------------------------------|-----|-----|------|--|
| | The second second state and the second second state of | DW package | | | 111 | |
| R _{0JA} Thermal resistance, junction-to-ambient | N package | All 8 outputs with equal power | | 108 | °C/W | |







INPUT SETUP AND HOLD WAVEFORMS

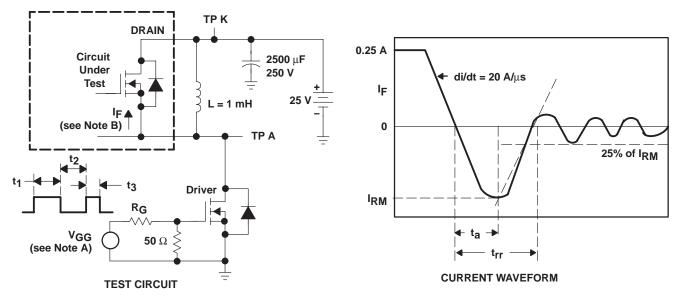


NOTES: A. Outputs DRAIN 1, 2, 5, and 6 low (PGND), all other DRAIN outputs are at 24 V. The word generator has the following characteristics: t_r ≤ 10 ns, t_f ≤ 10 ns, t_f ≤ 10 ns, t_g = 300 ns, pulsed repetition rate (PRR) = 5 kHz, Z_O = 50 Ω.
B. C_I includes probe and jig capacitance.

Jia _



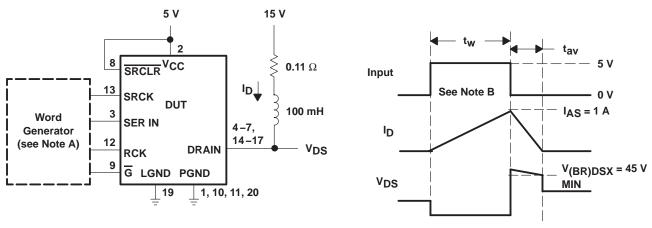
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PARAMETER MEASUREMENT INFORMATION

- NOTES: A. The V_{GG} amplitude and R_G are adjusted for di/dt = 20 A/ μ s. A V_{GG} double-pulse train is used to set I_F = 0.25 A, where t₁ = 10 μ s, t₂ = 7 μ s, and t₃ = 3 μ s.
 - B. The DRAIN terminal under test is connected to the TP K test point. All other terminals are connected together and connected to the TP A test point.

Figure 3. Reverse-Recovery-Current Test Circuit and Waveforms of Source-Drain Diode



SINGLE-PULSE AVALANCHE ENERGY TEST CIRCUIT

VOLTAGE AND CURRENT WAVEFORMS

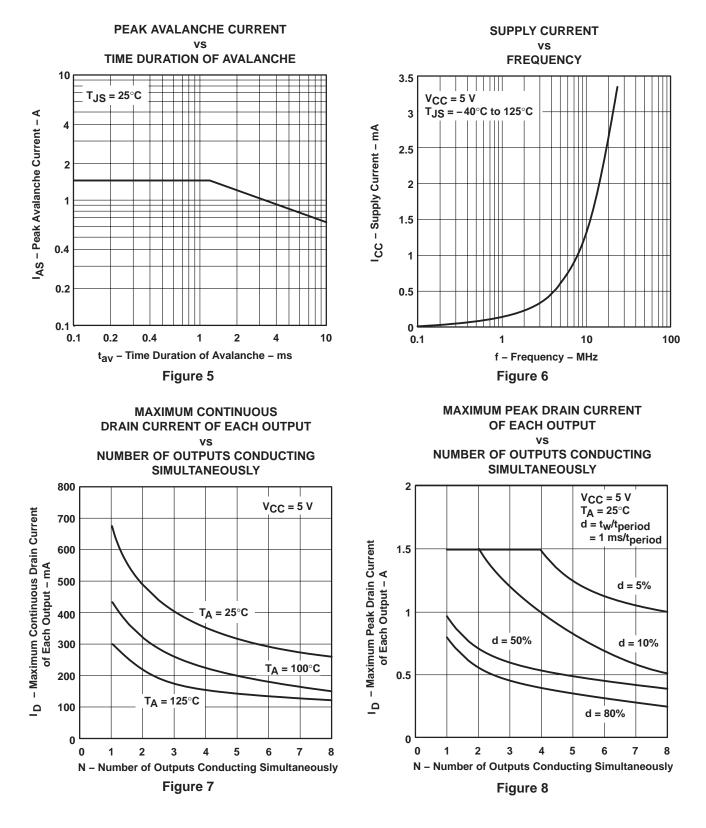
NOTES: A. The word generator has the following characteristics: $t_f \le 10 \text{ ns}, t_f \le 10 \text{ ns}, Z_O = 50 \Omega$. B. Input pulse duration, t_W , is increased until peak current $I_{AS} = 1 \text{ A}$. Energy test level is defined as $E_{AS} = I_{AS} \times V_{(BR)DSX} \times t_{av}/2 = 75 \text{ mJ}$, where t_{av} = avalanche time.

Figure 4. Single-Pulse Avalanche Energy Test Circuit and Waveforms



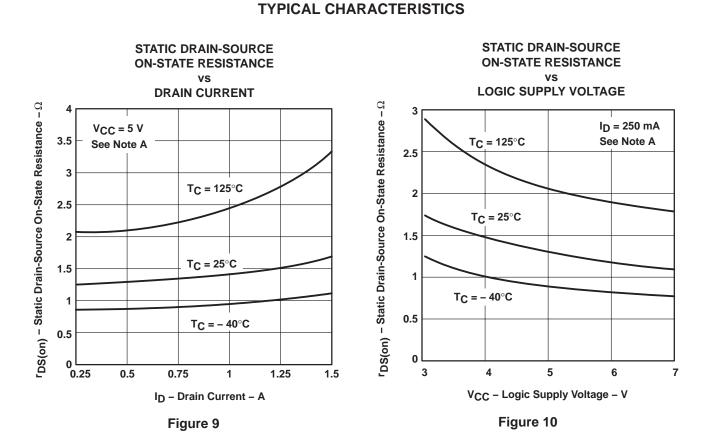
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TYPICAL CHARACTERISTICS





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700 tr 600 ^tPLH I_D = 250 mA 500 See Note A tf 400 300 200 ^tPHL

SWITCHING TIME vs FREE-AIR TEMPERATURE

50 T_A – Free-Air Temperature – °C

100

150

Figure 11

0

NOTE A: Technique should limit $T_J - T_C$ to 10°C maximum.

t - Switching Time - ns

100 - 50



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Revision History

| DATE | REV | PAGE | SECTION | DESCRIPTION |
|---------|-----|------|----------|------------------------------|
| 5/18/05 | В | 5 | Figure 1 | Changed SRCLR timing diagram |
| 10/1/96 | А | | — | — |
| 4/1992 | * | | | Original reversion |

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.





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PACKAGING INFORMATION

| Orderable Device | Status ⁽¹⁾ | Package Type | Package Drawing | Pins | Package Qty | Eco Plan ⁽²⁾ | Lead/ Ball Finish | MSL Peak Temp ⁽³⁾ | Samples (Requires Login) |
|------------------|-----------------------|--------------|--------------------|------|-------------|----------------------------|----------------------|------------------------------|-----------------------------|
| TPIC6595DW | ACTIVE | SOIC | DW | 20 | 25 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| TPIC6595DWG4 | ACTIVE | SOIC | DW | 20 | 25 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| TPIC6595DWR | ACTIVE | SOIC | DW | 20 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| TPIC6595DWRG4 | ACTIVE | SOIC | DW | 20 | 2000 | Green (RoHS & no Sb/Br) | CU NIPDAU | Level-1-260C-UNLIM | |
| TPIC6595N | ACTIVE | PDIP | N | 20 | 20 | Pb-Free (RoHS) | CU NIPDAU | N / A for Pkg Type | |

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



| *All dimensions are no | minal |
|------------------------|-------|
| | |

| Device | Package Type | Package Drawing | | SPQ | Reel Diameter (mm) | Reel Width W1 (mm) | A0 (mm) | B0 (mm) | K0 (mm) | P1 (mm) | W (mm) | Pin1 Quadrant |
|-------------|-----------------|--------------------|----|------|--------------------------|--------------------------|------------|------------|------------|------------|-----------|------------------|
| TPIC6595DWR | SOIC | DW | 20 | 2000 | 330.0 | 24.4 | 10.8 | 13.3 | 2.7 | 12.0 | 24.0 | Q1 |

TEXAS INSTRUMENTS

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PACKAGE MATERIALS INFORMATION

4-Jan-2013



*All dimensions are nominal

| Device | Package Type | Package Drawing | Pins | SPQ | Length (mm) | Width (mm) | Height (mm) |
|-------------|--------------|-----------------|------|------|-------------|------------|-------------|
| TPIC6595DWR | SOIC | DW | 20 | 2000 | 367.0 | 367.0 | 45.0 |

N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- \triangle The 20 pin end lead shoulder width is a vendor option, either half or full width.



DW (R-PDSO-G20)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M-1994.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).

D. Falls within JEDEC MS-013 variation AC.



LAND PATTERN DATA



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Refer to IPC7351 for alternate board design.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



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